

## Low Voltage, 2.7-6V Input, 1.5A, 1.2MHz Synchronous Step-Down Converter

The Future of Analog IC Technology

# DESCRIPTION

The MP2012 is a fu lly integrated, internally compensated 1.2MHz fixed frequency PWM step-down converter. It is idea I f or powering portable equipment that runs from a single cell Lithium-Ion (Li+) Battery, with an input range from 2.7V to 6V. The MP2012 can provide up to 1.5A of load current with output voltage as low as 0.8V. It can also operate at 100% duty cycle for low drop out applications. With peak current mode control and internal compensation, the MP2012 is stable with ceramic cap acitors and small indu ctors. Fault conditio n protection includes cy cle-by-cycle current limiting and thermal shutdown.

MP2012 is available in a small QFN6 (3x3 mm) package.

## **FEATURES**

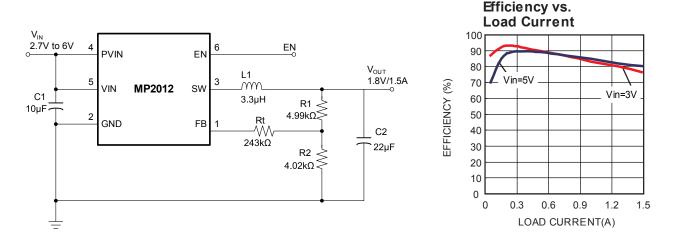
- 2.7-6V Input Operation Range
- Output Adjustable from 0.8V to VIN
- 1µA Max Shutdown Current.
- Up to 95% Efficiency
- 100% Duty Cycle for Low Dropout Applications
- 1.2MHz Fixed Switching Frequency
- Stable with Low ESR Output Ceramic Capacitors
- Thermal Shutdown
- Cycle-by-Cycle Over Current Protection
- Short Circuit Protection
- Available in QFN6 (3x3mm)

## **APPLICATIONS**

- DVD+/-R W Drives
- Smart Phones
- PDAs
- Digital Cameras
- Portable Instruments

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# **TYPICAL APPLICATION**





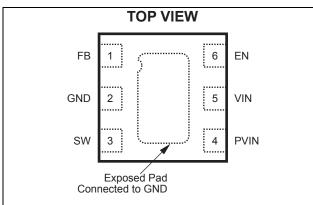
### **ORDERING INFORMATION**

Part Number*	Package	Top Marking	Free Air Temperature (T <sub>A</sub> )
MP2012DQ	QFN6(3x3mm)	9E	–40°C to +85°C

\* For Tape & Reel, add suffix –Z (e.g. MP2012DQ–Z).

For RoHS compliant packaging, add suffix -LF (e.g. MP2012DQ-LF-Z)

# PACKAGE REFERENCE



# ABSOLUTE MAXIMUM RATINGS (1)

PVIN, VIN to GND	–0.3V to + 6.5V
SW to GND	.–0.3V to V <sub>IN</sub> + 0.3V
EN, FB to GND	–0.3V to +6.5V
Operating Temperature	
Continuous Power Dissipati	on (T <sub>A</sub> = +25°C) <sup>(2)</sup>
	2.5W
Junction Temperature	150°C
Lead Temperature	260°C
Storage Temperature	–65°C to +150°C
	(-)

### Recommended Operating Conditions <sup>(3)</sup>

Supply Voltage V<sub>IN</sub>......2.7V to 6V Operating Junct. Temp (T<sub>J</sub>)..... –40°C to +125°C

### **Thermal Resistance** <sup>(4)</sup> **θ**<sub>JA</sub> **θ**<sub>JC</sub> QFN6 (3x3mm) .......50 .......50 ......

#### Notes:

1) Exceeding these ratings may damage the device.

- 2) The maximum allowable power dissipation is a function of the maximum junction temperature T J (MAX), the junction-toambient thermal resistance  $\theta_{JA}$ , and the ambient temperature T<sub>A</sub>. The maximum allowable continuous power dissipation at any ambient temperature is ca lculated by P D (MAX) = (T J (MAX)-T<sub>A</sub>)/ $\theta_{JA}$ . Exceeding the maximum allowable power r dissipation will cause excessive die temperature, and the regulator will g o into thermal shutdown. Internal thermal shutdown circuitr y pr otects the device from permanent damage.
- The device is not guarant eed to function outside of its operating conditions.
- 4) Measured on JESD51-7, 4-layer PCB.

# ELECTRICAL CHARACTERISTICS (5)

### $V_{IN} = V_{EN} = 3.6V$ , $T_A = +25^{\circ}C$ , unless otherwise noted.

Parameters Conditio	n	Min	Тур	Мах	Units
Supply Current	$V_{EN} = V_{IN}, V_{FB} = 0.9V$	600		750	μA
Shutdown Current	$V_{EN} = 0V, V_{IN} = 6V$		0.01	1	μA
Thermal Shutdown Trip Threshold	Hysteresis = 20°C	150			С°
EN Trip Threshold	$-40^{\circ}C \le T_A \le +85^{\circ}C$	0.3	1.0	1.5	V
EN Input Current	$V_{EN} = 0V$		0.1	1.0	μA
EN Input Current	$V_{EN} = 6V$		6		μA
IN Undervoltage Lockout Threshold Risi	ng Edge	2.15	2.40	2.65	V
IN Undervoltage Lockout Hysteresis			160		mV
Regulated FB Voltage	T <sub>A</sub> = +25°C -40°C≤ T <sub>A</sub> ≤ +85°C	0.784 0.776	0.800 0.800	0.816 0.824	V
FB Input Bias Current	V <sub>FB</sub> = 0.8V	-50	-2	+50	nA
SW PFET On Resistance	I <sub>SW</sub> = 100mA	0.18	0.25	0.28	Ω
SW NFET On Resistance	I <sub>SW</sub> = -100mA	0.14	0.2	0.24	Ω
SW Leakage Current	V <sub>EN</sub> =0V; V <sub>IN</sub> =6V V <sub>SW</sub> =0V	-1 0.1		1	μA
SW Leakage Current	V <sub>EN</sub> =0V; V <sub>IN</sub> =6V V <sub>SW</sub> =6V	-5 1.5		5	μA
SW PFET Peak Current Limit	Duty Cycle=100% Duty Cycle=50% <sup>(6)</sup>	2.1	3.0 3.5	А	
Switching Frequency		1.0	1.2	1.4	MHz

Notes:

5) Production test at +25°C. Specifications over the temperature range are guaranteed by design and characterization.

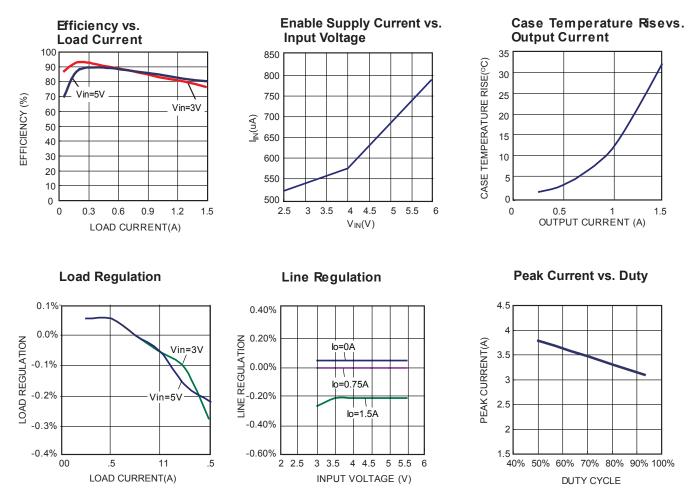
# **PIN FUNCTIONS**

Pin #	Name	Description		
1 FE	3	Feedback input. An external resistor divider from the output to GND, tapped to the FB pin sets the output voltage.		
2	GND, Exposed Pad	Ground pin. Connect exposed pad to grou nd plane f or proper t hermal performance.		
3	SW	Switch node to the inductor.		
4	PVIN	Input supply pin for power FET.		
5	VIN	Input Supply pin for controller. Put small decoupling ceramic near this pin.		
6	EN	Enable input, "High" enables MP2012. EN is pulled to GND with 1Meg internal resistor.		



# **TYPICAL PERFORMANCE CHARACTERISTICS**

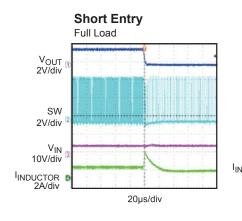
 $V_{IN}$  = 5V,  $V_{OUT}$  = 1.8V, L=3.3uH,  $T_A$  = +25°C, unless otherwise noted.

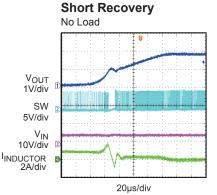




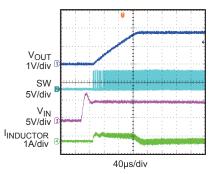
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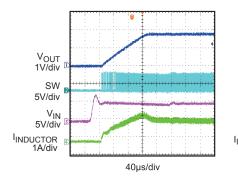




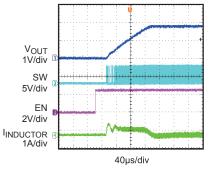
#### Power Up without Load

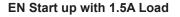


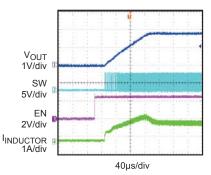
Power Up with 1.5A Load



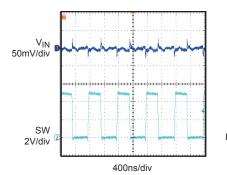
EN Start Up without Load

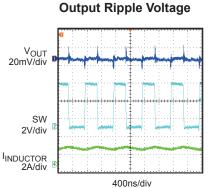
















# FUNCTION BLOCK DIAGRAM

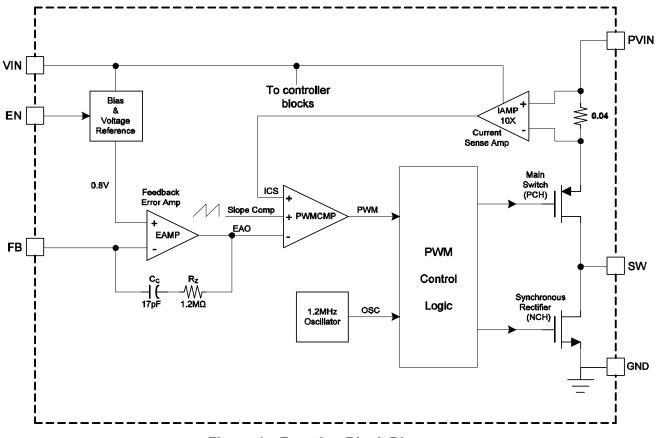


Figure 1—Function Block Diagram



# **OPERATION**

The MP2012 is a fixed frequency 1.2MHz current mode 1.5A step-down converter, optimized for low voltage, Li-lon batt ery powere d applications where high efficiency a nd small size are critica I. MP2012 integrates a high side PFET main switch and a low side synchr onous rectif ier. It always operates in continuo us conduction mode, simplifies the control scheme and eliminates th e random spectrum noise due to discontinuous conduction mode.

The steady state duty cycle D for this mode can be calculated as:

$$D = T_{ON} \times f_{OSC} \times 100\% \approx \frac{V_{OUT}}{V_{IN}} \times 100\%$$

Where  $T_{ON}$  is the main switch on time and f <sub>OSC</sub> is the oscillator frequency (1.2MHz typ.).

### **Current Mode PWM Control**

Slope compensated cur rent mode PWM control provides stable switch ing and cycle-by-cycle current limiting for superior loa d and lin е response a s well as protection o f the internal main switch and synchronous r ectifier. Th e MP2012 switches at a consta nt frequen cy (1.2MHz) and modulates the ind uctor peak current to regulate the output voltage. Specifically, for each cy cle the PW M controller forces the inductor pe ak current to an inter nal referen ce level derived from the feedback err or voltage. At normal operation, the main switch is turned on at each rise edge of the internal oscillator, and remains on for a certain period of time to ramp up the inductor current. A s soon as the inductor current reaches the r eference le vel, the main switch is turned off and immediately t he synchronous rectifier will be turned on to provide the inductor current. In forced PW M mode, the synchronous rectif ier will stay on until the ne xt oscillator cycle.

### **Dropout Operation**

The MP2012 allows the main switch to remain on for more than one switching cycle to increase the duty cycle when the input voltage is dropping close to the output voltage. When the duty cycle reaches 10 0%, the main switch is held on continuously to deliver current to the output up to the PFET current limit. In this case, the output voltage becomes the input voltage minus the voltage drop across the main switch and the inductor.

### **Maximum Load Current**

The MP201 2 can oper ate down to 2.5V inp ut voltage; however the ma ximum load current decreases at lower input due to a L arge IR dro p on the main switch a nd synchronous rectif ier. The slope compensation signal red uces the peak inductor current as a function of the duty cycle to prevent sub-harmonic oscillations a t duty cycles greater than 50%. Co nversely, th e current limit increases as the duty cycle decreases.

### **Short Circuit Protection**

When shor t circuit or over current condition happens, and FB is lower than ab out 0.3V, the MP2012 enters fold ba ck mode. T he oscillato r frequency is reduced to prevent the inducto r current from increasing beyond the PFET current limit. The PFET current limit is also reduced to lower the short circuit current. The frequency and current limit will return to the normal values once the short circuit cond ition is removed and the feedback voltage approaches 0.8V.



### **APPLICATION INFORMATION**

#### **Output Voltage Setting**

The external resistor divider sets the output voltage.

$$V_{\text{out}} = 30.8 \quad \left( \right) + \frac{R_1}{R_2}$$

Rt is recommended when output voltage is high, as the Figure 2 shows.

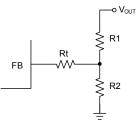


Figure 2—Feedback Network

Table 1 lists the recommended resistor value for common output voltages.

 Table 1—Resistor Selection vs. Output

 Voltage Setting

V <sub>OUT</sub> /	<b>Rt</b> / kΩ	<b>R1</b> / kΩ	<b>R2</b> / kΩ	<b>L1</b> / μΗ	<b>C2</b> / μF
1.2	300	4.99	10	2.2	22
1.8V	243	4.99	4.02	3.3	22
2.5V	100	121	57.6	3.3	22
3.3V	100	121	39	3.3	22

#### **Inductor Selection**

A 1 $\mu$ H to 10 $\mu$ H inductor with DC current rating a t least 25% higher than the maxi mum load current is recommended for most applications. For be st efficiency, t he inductor DC resistance shall b e <200m $\Omega$ . See Table 2 for recommende d inductors and manufacturers. For most design s, the inducta nce value can be derived from th e following equation:

$$L = \frac{V_{OUT} \times \left(V_{IN} - V_{OUT}\right)}{V_{IN} \times \Delta I_L \times f_{OSC}}$$

Where  $\Delta I_L$  is inductor ripple current. Choose inductor ripple current approximately 30% of the maximum load current, 1.5A.

The maximum inductor peak current is:

$$I_{L(MAX)} = I_{LOAD} + \frac{\Delta I_{L}}{2}$$

Manufacturer	Part Number	Inductance (µH)	Dimensions LxWxH (mm <sup>3</sup> )		
Cooper	SD25-3R3	3.3	5.2X5.2X2.5		
Toko	D63LCB#A921 CY-3R6M	3.6	6.3X6.2X3		
ток	SLF7045T- 3R3M2R5-PF	3.3 7X72	<b>X</b> 4.5		

#### Table 2—Suggested Inductors

#### Input Capacitor C<sub>IN</sub> Selection

The input capacitor red uces the surge curren t drawn from the input and switching noise from the device.

Ceramic capacitors wit h X 5R or X7R dielectrics are highly recommende d because of their low ESR and small temperature coefficients. For r most applications, a  $10\mu$ F capacitor is sufficient.

#### **Output Capacitor COUT Selection**

The output capacitor keeps output voltage ripple small and ensures reg ulation loop stable. The output capacitor impedance shall be low at the switching fr equency. Ceramic capacitors with X5R or X 7R dielectrics are recommended. For forced PWM mode op eration, the output ripple  $\Delta V_{OUT}$  is approximately:

$$\Delta \Psi_{\text{out}} = \frac{V_{\text{out}} \cdot \left(V_{\text{IN}} - V_{\text{out}}\right)}{V_{\text{IN}} \cdot f_{\text{osc}} - L} \bigcirc \mathbb{R}_{\text{ESR}} + \frac{1}{8} \cdot \frac{1}{f_{\text{osc}} \cdot C_{\text{out}}}$$

For most applications, a 22  $\,\mu\text{F}$  capacitor is sufficient.

#### **Thermal Dissipation**

Power dissipation shall be considered when operates MP2012 at ma ximum 1.5A out put current. If the junct ion temperature rises above 150°C, MP2012 will be shut d own by intern al thermal protection circuitry.

The junction-to-ambient thermal resistance of the 6-pin QFN ( $3mm \times 3 mm$ )  $R_{\Theta JA}$  is 50 °C/W. The maximum a llowable power dissipat ion is about 1.6W when MP2012 is operating in a 70 °C ambient temperature environment:

$$PD_{MAX} = \frac{150^{\circ}C - 70^{\circ}C}{50^{\circ}C / W} = 1.6W$$

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IN and GND pins. The external feedback

resistors shall be placed next to

from the feedback network.

direct and wide traces. Input capa citors should

be placed as close as p ossible to the respective

Keep the switching no des SW sh ort and away

the FB pins.

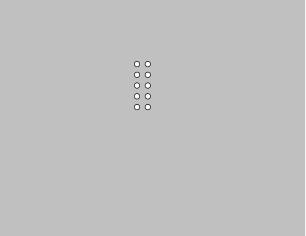
#### **PC Board Layout**

PCB la yout is very important to achieve stable operation. Please follo w these g uidelines a nd take Figure2 for references.

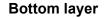
The high current paths (GND, IN and SW) should be placed very close to the device with short,

GND C2 L.1 PVI 5 0 6 Œ 00 R3 R1 R4 R2 C1 C4 VIN GND VOUT

GND



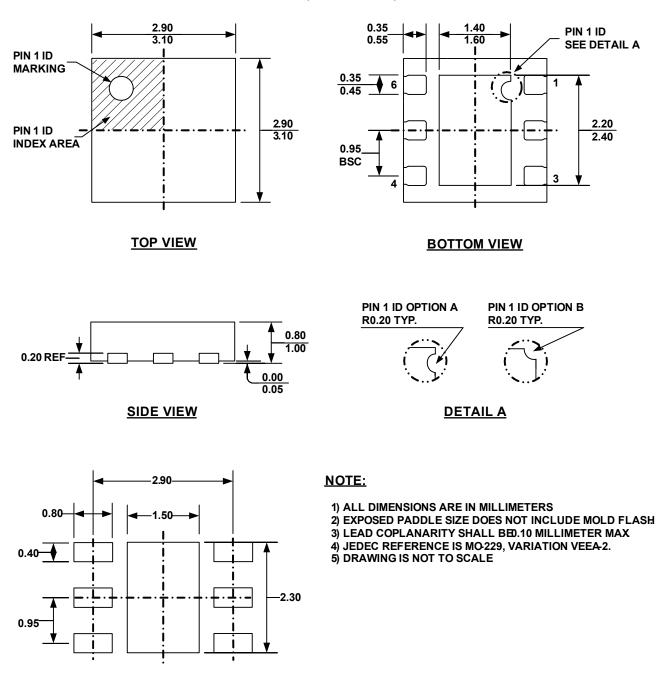
Top layer



### Figure 3—PCB Layout



# PACKAGE INFORMATION



### QFN6 (3mmx3mm)

**RECOMMENDED LAND PATTERN** 

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